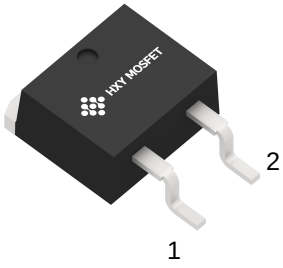
IDK08G120C5XTMA1

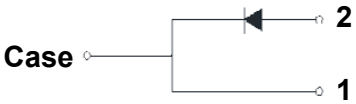
Silicon Carbide Schottky Diode

Features

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F



TO-263N



Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives

Part Number	Package	Qty(PCS)
IDK08G120C5XTMA1	TO-263N	800

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V	
V_{RSM}	Surge Peak Reverse Voltage	1200	V	
I_F	Continuous Forward Current	23.9 11.3 8	A	T_C=25˚C T_C=135˚C T_C=152.5 ˚C
I_{FRM}	Repetitive Peak Forward Surge Current	48	A	T_C=25˚C, t_p = 10 ms, Half Sine Wave
I_{FSM}	Non-Repetitive Peak Forward Surge Current	96	A	T_C=25˚C, t_p = 10 ms, Half Sine Wave
P_{tot}	Power Dissipation	106 46	W	T_C=25˚C T_C=110˚C
T_J , T_{stg}	Operating Junction and Storage Temperature	-55 to +175	˚C	
$\int i^2dt$	i²dt value	46.08	A^2s	T_C=25˚C, t_p = 10 ms, Half Sine Wave

Electrical Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V_{DC}	DC Blocking Voltage	1200			V	
V_F	Forward Voltage		1.45 1.99	1.7 2.5	V	I_F = 8 A T_J=25°C I_F = 8 A T_J=175°C
I_R	Reverse Current		3.5 17	50 100	μA	V_R = 1200 V T_J=25°C V_R = 1200 V T_J=175°C
Q_C	Total Capacitive Charge		38		nC	V_R = 800 V T_J = 25°C
C	Total Capacitance		595 38 30		pF	V_R = 0 V, T_J = 25°C, f = 1 MHz V_R = 400 V, T_J = 25°C, f = 1 MHz V_R = 800 V, T_J = 25°C, f = 1 MHz
E_C	Capacitance Stored Energy		20		μJ	V_R = 800 V

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.41	°C/W

Typical Performance

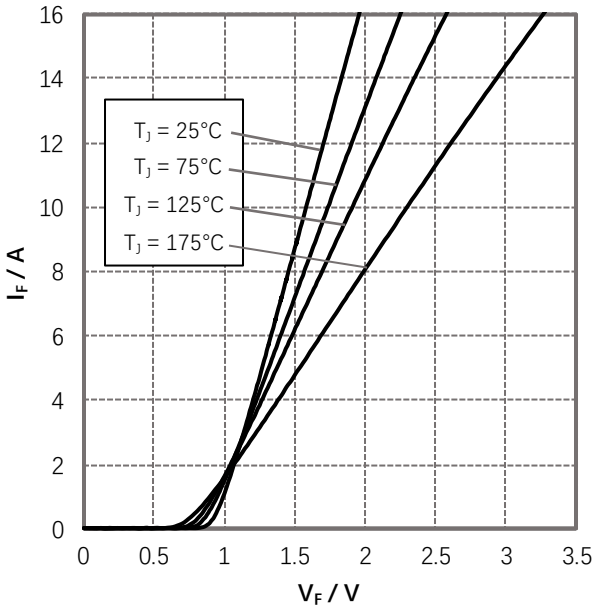


Figure 1. Forward Characteristics

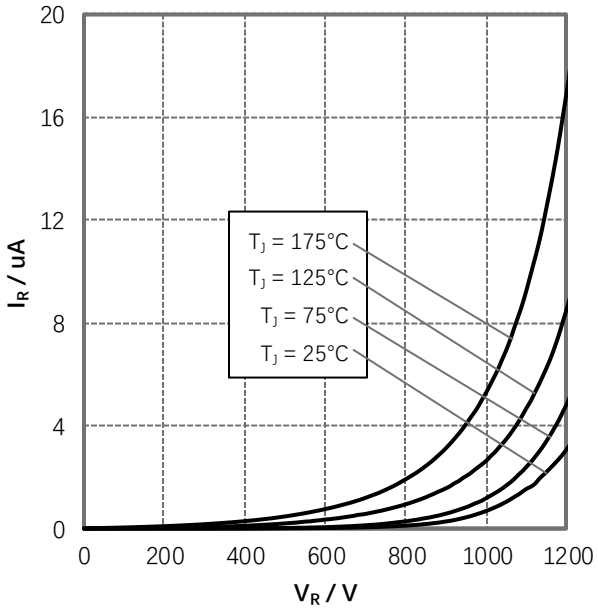


Figure 2. Reverse Characteristics

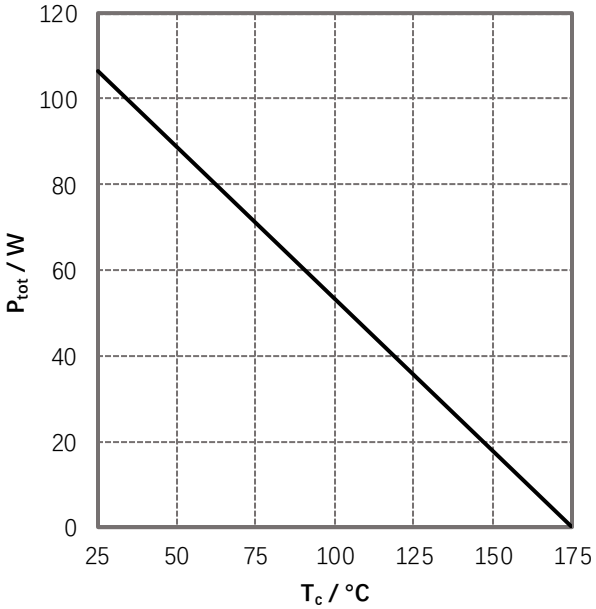


Figure 3. Power Derating

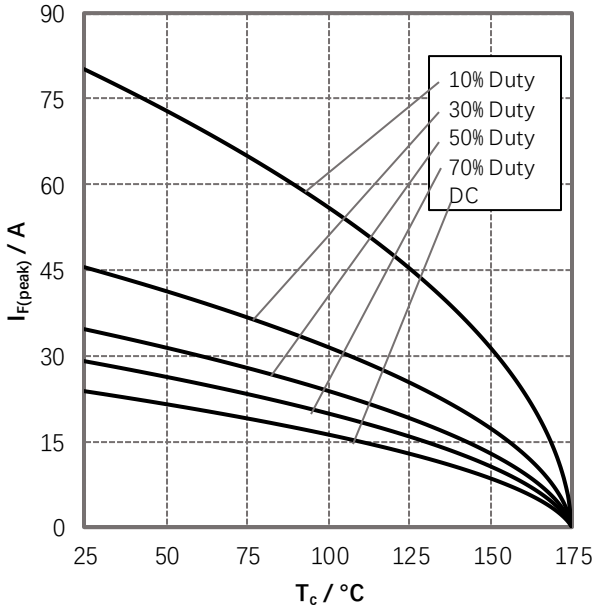


Figure 4. Current Derating

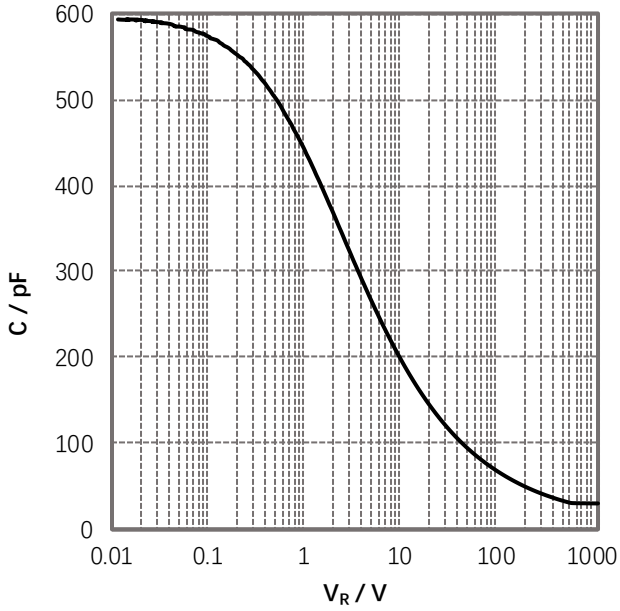


Figure 5. Capacitance vs. Reverse Voltage

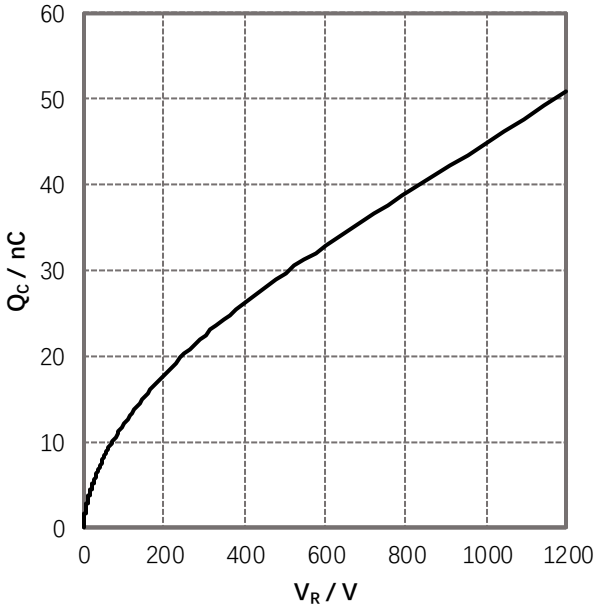


Figure 6. Total Capacitance Charge vs. Reverse Voltage

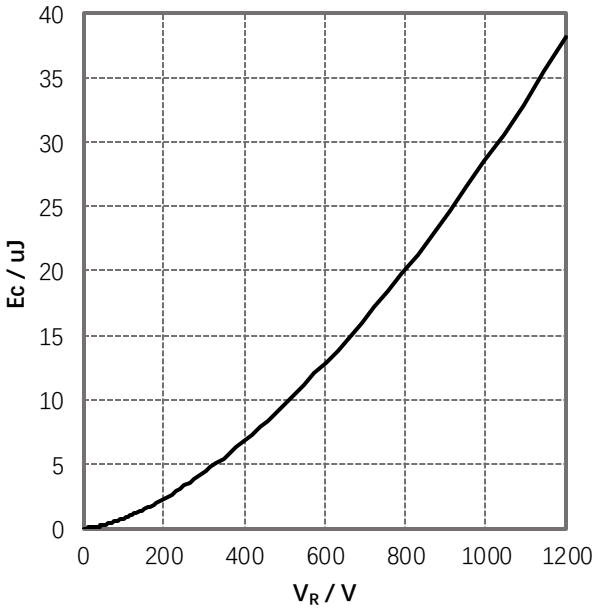


Figure 7. Capacitance Stored Energy

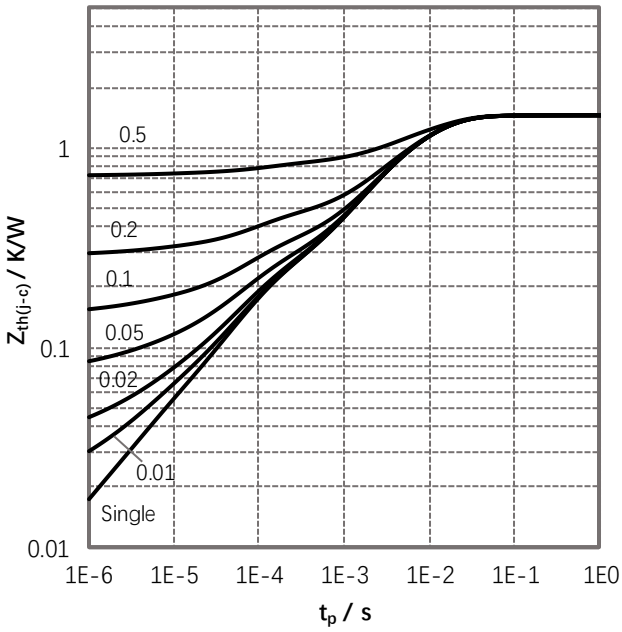
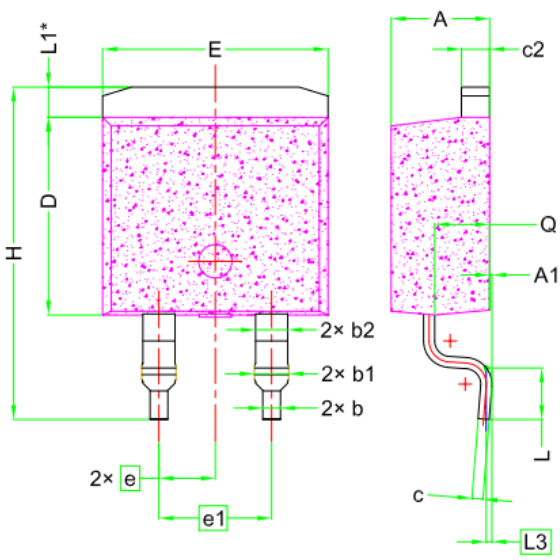
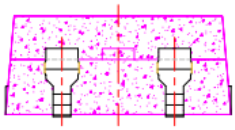


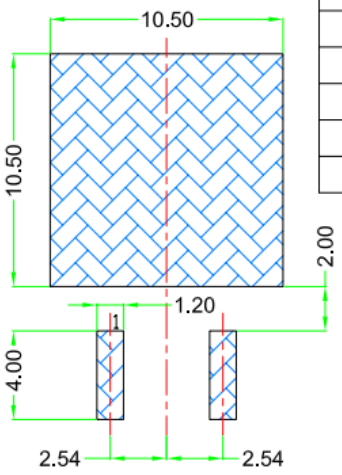
Figure 8. Transient Thermal Impedance

Package Information
TO-263N





Land Pattern
(Only for Reference)



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
e1	5.08 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

Note:
1. All Dimensions Are In mm.
2. Dimension D & E Do Not Include Mold Flash.
   Mold Flash Shall Not Exceed 0.127mm Pre Side.
   These Dimensions Are Measured At The Outermost
   Extreme Of The Plastic Body.
3. Thermal Pad Contour Optional Within Dimensions E, L1, D1 & E1.
4. Dimension D1 & E1 Establish A Minmum Mounting Surface for
   The Thermal Pad.
5. "*" is reference .

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